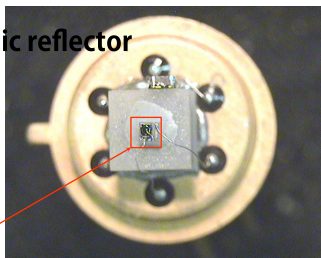


## Features

- High reliability
- Superior linearity
- Thermo stability
- Easy-to-use detector/amplifier modules are also available

- Parabolic reflector



Photodiode CHIP

## Description

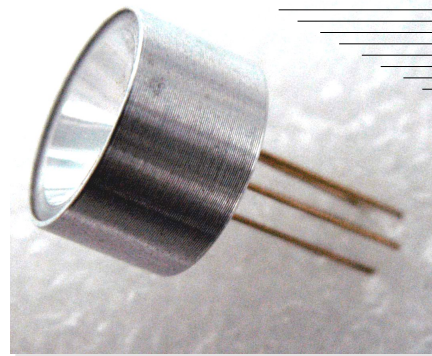
Photodiode **PD36-05-TEC-PRW** is a model of [photodetector](#) for detection of radiation at room temperature in the Middle Infrared (Mid-IR) spectral range from 1500 to 3800 nm.

Photodiode **PD36-05-TEC-PRW** has thermo electric cooler (TEC) and thermistor for a control of temperature. Components are integrated inside the standard 9.2 mm TO-5 package with TEC, parabolic reflector (PR) and window (W).

Diameter of the photosensitive area of **PD36-05-TEC-PRW** is 500  $\mu\text{m}$ . High speed of response makes it possible for detection of modulated radiation of laser diodes (LDs) and light-emitting diodes (LEDs). PR allows to increase detectivity of the photodiode by a factor of 10 in the case of parallel beam of radiation.

## General characteristics

Package	Parameter	Symbol	Value	Unit
TO-5 with TEC PR W	Sensitive area diameter	d	0.5	mm
	Weight	m	3.65	g
	Operating temperature	T <sub>opr</sub>	-20...+40	°C
	Window material	sapphire glass		
	Cooling	one-stage TE-cooled		
	Soldering temperature	T <sub>s</sub>	+230	°C
	Storage temperature	T <sub>stg</sub>	-20...+50	°C
	Maximum reverse bias voltage	V	-1.0	V
	Size	D	10.5	mm
H		23.0		



## Applications

- Environment measurements
- Infrared spectrophotometry
- Laser detection
- Analytical instruments

## Accessories (optional)

- [Amplifier with temperature controller AMT-07M](#)

▼ **Electrical and optical characteristics**

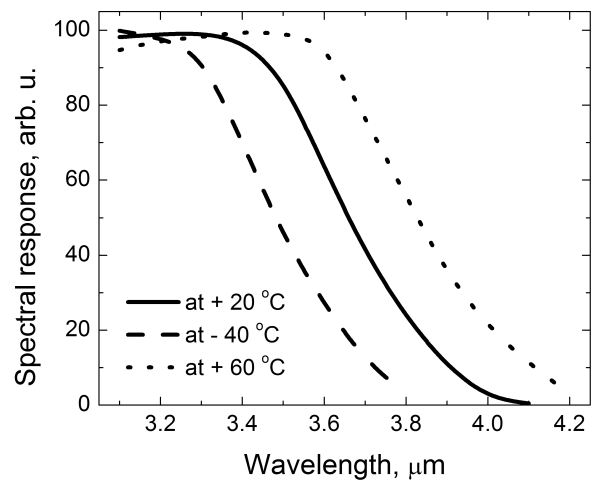
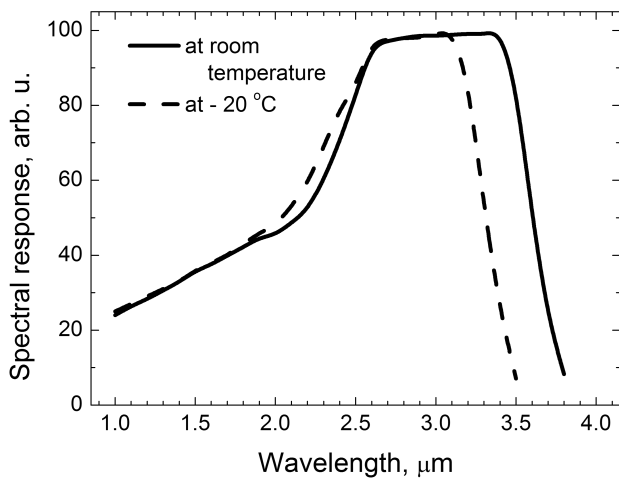
Parameter	Symbol	Condition	Element temperature			Unit
			-20°C	0°C	+20°C	
Spectral sensitivity range	$\lambda$	at level 10%	1.5* - 3.6	-	1.5* - 3.8	$\mu\text{m}$
Peak sensitivity wavelength	$\lambda_p$	at level 90%	2.5 - 3.3	-	2.6 - 3.4	$\mu\text{m}$
Photo sensitivity	S	at $\lambda_p$	1.0 - 1.2			A/W
Detectivity	$D^*$	at $\lambda_p$	$[0.6 - 1.0] \cdot 10^{10}$	-	$[3 - 6] \cdot 10^9$	$\text{cm} \cdot \text{Hz}^{1/2} \cdot \text{W}^{-1}$
Dark current	$I_d$	V = -0.2 V	90 - 150	-	200 - 600	$\mu\text{A}$
		V = -0.4 V	150 - 300	-	450 - 800	
Capacitance	C	V = 0 V, f = 1 MHz	300 - 1300			pF
Rise time	$t_r$	V = 0 V, $R_L = 50 \Omega$	50 - 150			ns
Fall time	$t_f$					
Shunt resistance	$R_0$	V $\approx$ -10 mV	500 - 3000	-	80 - 700	$\Omega$
Noise equivalent power	NEP	at $D^*$	$[14.8 - 8.9] \cdot 10^{-12}$	-	$[3.0 - 1.5] \cdot 10^{-11}$	$\text{W} \cdot \text{Hz}^{-1/2}$

▼ **TEC TO506.1MC0400710.TB103 parameters (without load)**

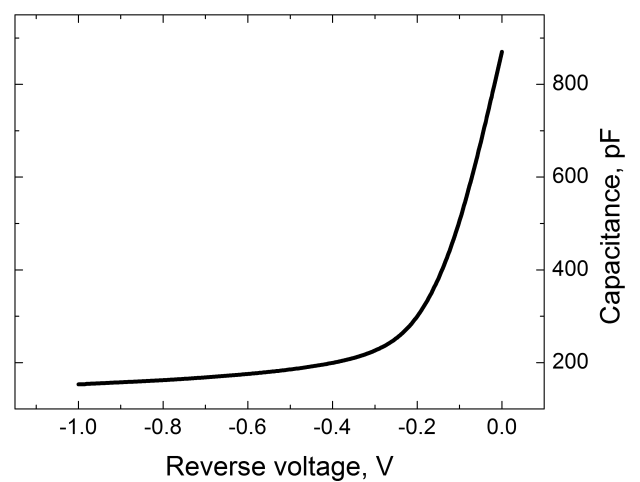
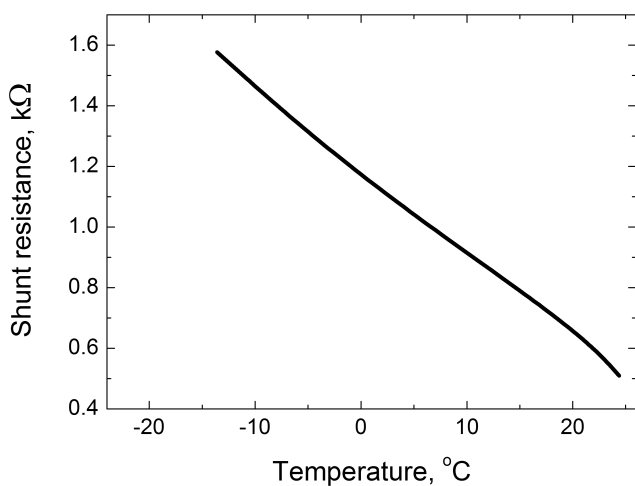
Parameter	Symbol	Condition	Value	Unit
Current	$I_{\text{max}}$	$\Delta T_{\text{max}}$	1.50	A
Voltage	$U_{\text{max}}$	$\Delta T_{\text{max}}$	0.80	V
Cooling energy	$Q_{\text{max}}$	-	1.30	W
Temperature range	$\Delta T_{\text{max}}$	vacuum	70	K
Thermistor resistance	$R_t$	at +20°C	10.00	k $\Omega$

\* Not at level 10%

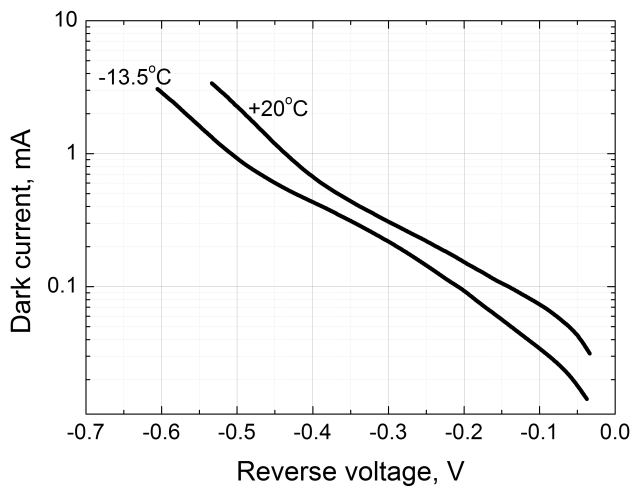
▾ Spectral response



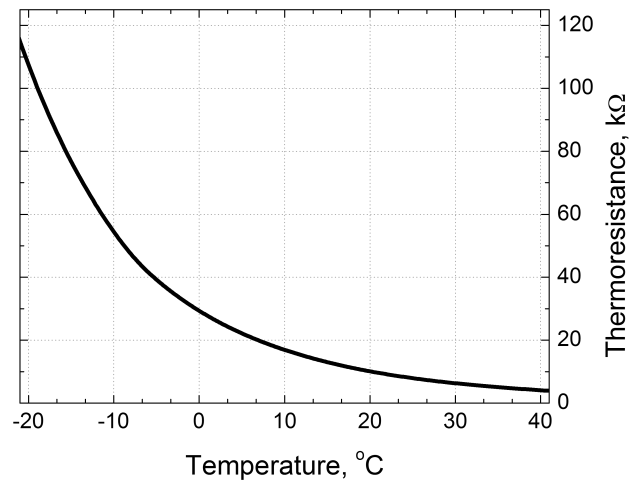
▾ Shunt resistance vs. element temperature    ▾ Capacitance vs. reverse voltage



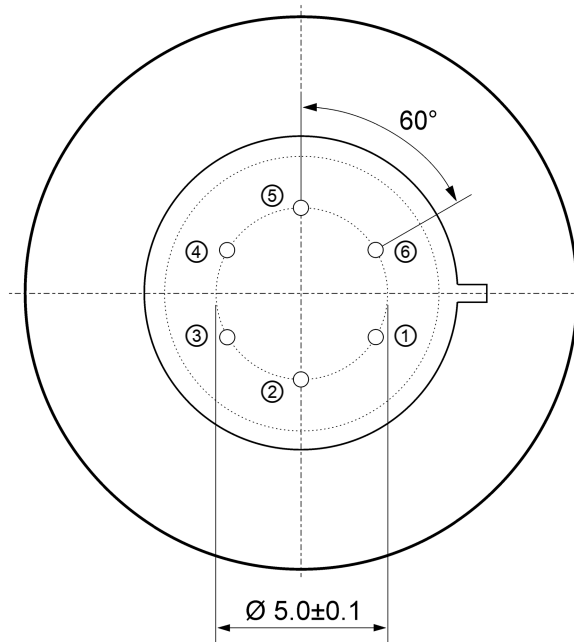
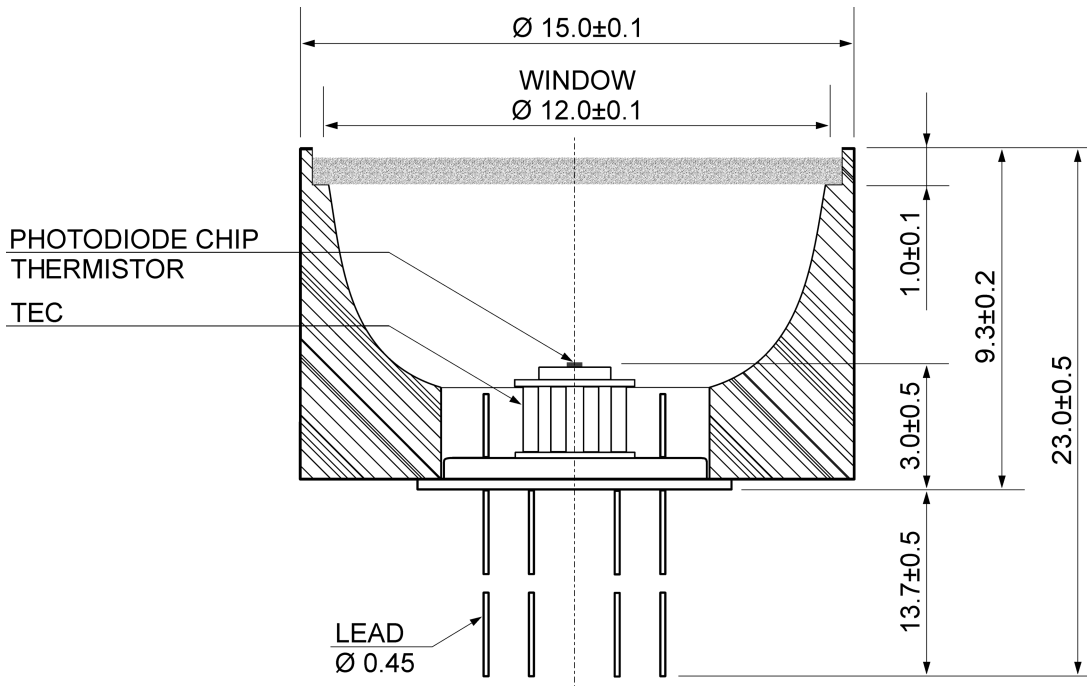
▼ Dark current vs. reverse voltage



▼ Thermoresistance vs. temperature



▼ TO-5 package with TEC & PR dimensions (unit: mm)



Pin	Description
①	TEC (anode)
②	Detector (anode)*
③	Detector (cathode)*
④	Thermistor TC103
⑤	
⑥	TEC (cathode)

\*Special order: the pin polarity can be changed.